

On page 6, line 18, after "formation" insert --of-- and insert commas after "is" and "course";

On page 6, line 26, after "depicting" delete "of";

On page 9, line 16, change the comma after "1-6" to a semicolon and insert a comma after "therefore";

On page 9, line 17, change "FIG." to --FIGS.--.

IN THE CLAIMS:

Please amend claims 23-25, and 27-28 as follows:

Subt F1
23. (Amended) A gate stack including a non-crystalline metallic silicide film [in a non-annealed state].

24. (Amended) A gate stack, including a crystalline metallic silicide film [in an annealed state] wherein said metallic silicide film is substantially devoid of silicon clusters.

B1
Sub D1
25. (Amended) A gate stack on a dielectric layered semiconductor substrate, comprising:
a polysilicon layer disposed over said dielectric layered semiconductor substrate;
a non-crystalline metallic silicide film [in a non-annealed state] disposed over said polysilicon layer; and
a dielectric cap on said non-crystalline metallic silicide film [formed at a sufficiently low temperature that said metallic silicide film remains in said non-annealed state].

Subt F4
27. (Amended) The gate stack structure of claim 26 wherein said a gate stack includes a [non-annealed] non-crystalline metallic silicide film.